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Patents

- 8,230,158 Memory devices and methods of storing data on a memory device 7/24/2012
- 7,835,187 Boosting seed voltage for a memory device 11/16/2010
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- 5,566,194, Method and apparatus to improve read reliability in semiconductor memories, 10/15/1996
- 5,455,800, Apparatus and a method for improving the program and erase performance of a flash EEPROM memory array, 10/3/1995
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- 5,386,388, Single cell reference scheme for flash memory sensing and program state verification, 1/31/1995
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